

Publisher Correction: 2D fin field-effect transistors integrated with epitaxial high-*k* gate oxide

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 Check for updates

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In the version of this article initially published, there were labelling errors in Fig. 2e(i), where the red text currently reading “004” appeared as “006,” and in Fig. 4c, where the y-axis label currently reading “IDS (mA μm^{-1})” appeared as “IDS ($\mu\text{A} \mu\text{m}^{-1}$).” The errors have been corrected in the HTML and PDF versions of the article.

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